

Structural and Electronic Properties of Metal-Encapsulated Silicon Clusters in a Large Size Range

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MSi_n ($M = W, Os, O, P, C, \dots$), $ab initio$ calculations for $3 \leq n \leq 20$.

MSi_n , w
 Si_n , Tw
 $M@Si_n$

$10 \leq n \leq 16$. Tw
fi

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Tw fi $7 \cdot I$

w w $6-311 + G(d)$,

MSi_n , $Os@Si_{14}$, Tw Si_n

$(DB) 2 \cdot 4$ MSi_n

Tw Si_n Tw $I \cdot Tw$ w

A $(SiH_4) w$ M H
 M^+ ($M = Hf, Tw, \dots, I, \dots$) $MSi_n H_x$

$(x \leq 4, n) \cdot E$ w fi MSi_n $n = 14, 13, 12, 11, 9$

$MSi_n H_x$ Tw fi Tw $EE =$

M Tw $E[Si_n] + E[M] - E[MSi_n]$, $E[Si_n]$ fi

Si_n 5 , $ab initio$ w $(HOMO)$ (LMO)

WSi_{12} Tw $BLSP$ $9 \cdot 11 \cdot A$

w Si_n fi M (\dots) $HOMO$

MSi_n $? (2)$ $? (3)$ MSi_n w LMO 0.50 M DB $HOMO$

A $ab initio$ w $11, 12 \cdot Tw$ 2.93 2.70 \AA M

$(M = W, Os, O, P, C, \dots)$ $MSi_n s$ Tw M Si_n

$(3 \leq n \leq 20)$ Tw w 5 Tw $II \cdot Tw$

w $B3LYP$ $(B$ L $-P$) $F \cdot 1$ M Si_n

$6 \cdot P$ L $L2D$ $F \cdot 2 \cdot A$ fi $M \neq$ 6

$LanL2DZ(d)$ M WSi_3 , $PtSi_3$, $CoSi_9$, DB H, w

TABLE I. Si_n $M\text{Si}_n$ Tw $M@Si_{13}$:
 w $M@Si_{16}$ w $M@Si_{20}$. tri : $;$ $tetra$: $;$ p : $;$ b : $;$
 h : $;$ c : $;$ d : $;$ f : $;$ hp : $;$ FK : F $-K$.

I			
Si_3 8	D_{3d}	$, C_{2v}$	C_{3v} ,
Si_9 8	C_{2v} tri	$, D_{4h}$ $tetra$	$, D_{4d}$ $tetra$
Si_{10} 8	C_{3v}	$, D_{3h}$	tri
Si_{12} 3,5	D_{5h} p $, D_{5d}$ p	$, T_d$,
Si_{14} 9	C_{3v} tri	$, D_{4d}$	$tetra$
Si_{15} 10	b $, C_{2v}$	tri	
Si_{16} 9	D_{6h} h $, D_{6d}$ h	$, I_h$	
Si_{20}	c, d, f $, D_{7h}$ hp	$, D_{6h}$	h
	$f, c1, c2$		
	f FK	$, h$	
	I_h		

w WSi_n WSi_nH_x $n = 3$ (30%) 5 . Tw w Tw Si_n 13 , w W@Si_{10} ,
 WSi_n W@Si_n $\Delta E = E_{\text{exo}} - E_{\text{endo}} =$ W@Si_n W@Si_{10} ,
 $-0.50, 0.39, 1.63,$ ≈ 6 eV ($-$ $. H$,
 D_{6h}) $n = 3, 9, 10, 12,$, $n = 12, w$
 Tw $M@Si_n$ $-$
 $. \text{Tw}$ $M-$ $n = 10$ $n = 16. \text{Tw}$ $-$
 $\text{Os@Si}_{10}, w$ C_{3v} $-$
 w $O -$ $-$

TABLE II. Tw (NDB_{theor}) (NDB_{expt}) 5 DB , HOMO-L MO (),
 H , EE (), BE (, eV/), M $M-$ Si_n $. \text{Tw}$ L
 $. A$ Pt@Si_n $-$ $M@Si_n$ ($n = 17$ 10 , 18, 20) w DB .
 $2\mu_B w$

C								
M-	Si _n	NDB _{theor}	NDB _{expt}	G		EE	BE	C
WSi ₃		0	0	0.95	<i>L</i>	5.43	3.44	−0.41
PtSi ₃		11	...	1.38	<i>L</i>	4.35	3.33	−0.10
W@Si ₉		9		1.19	<i>L</i>	5.14	3.42	−2.14
CoSi ₉		1	0	0.34	<i>L</i>	3.96	3.12	0.49
W@Si ₁₀		6		1.39	<i>L</i>	5.09	3.50	−1.74
Os@Si ₁₀		0	...	1.48	<i>H</i>	5.60	3.55	−1.19
Ru@Si ₁₀		2	...	0.72	<i>L</i>	4.21	3.42	−1.26
Fe@Si ₁₀		0	...	0.25	<i>L</i>	2.27	3.25	−0.30
W@Si ₁₂		0	0	1.38	<i>H</i>	8.64	3.69	−1.74
Zr@Si ₁₂ (<i>C</i> ₁)		8		0.78	<i>L</i>	4.81	3.40	−0.45
Os@Si ₁₂ (<i>D</i> _{6h})		0	...	1.10	<i>H</i>	8.36	3.67	−1.23
W@Si ₁₄ (<i>f</i>)		0	...	0.38	<i>L</i>	8.74	3.70	−1.93
Zr@Si ₁₄ (<i>dbhpa</i>)		1	0	0.65	<i>L</i>	6.34	3.54	−1.97
Zr@Si ₁₄ (<i>dbhpb</i>)		0	0	1.23	<i>H</i>	6.18	3.53	−2.13
Os@Si ₁₄ (<i>c</i>)		0	...	1.63	<i>H</i>	7.19	3.60	−1.63
W@Si ₁₅ (<i>f</i>)		0	...	0.79	<i>H</i>	10.06	3.71	−2.04
W@Si ₁₆ (<i>f</i>)		1	...	1.11	<i>L</i>	10.22	3.73	−2.13
Zr@Si ₁₆ (<i>f</i>)		0	...	1.52	<i>H</i>	9.59	3.69	−2.19
W ₂ @Si ₂₀		0	...	0.55	<i>H</i>	16.75	3.65	−1.95
O	6-311 + <i>G</i> (<i>d</i>)			, w	LanL2DZ(<i>d</i>)		<i>dbhpa</i>	.

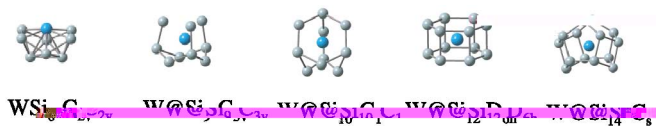


FIG. 1 (). G Si_n W₂@Si₂₀. T F Cr@Si₁₂ Zr@Si₁₆ M@Si₁₅ (M = W, Zr, Mo, Os, Pt) W@Si₁₂. T Mo@Si₁₂ Os@Si₁₅ Pt@Si₁₄, f, w

2.39 2.49 Å 2.36 2.43 Å, Zr@Si₁₄ C₁ (dbhpa) T w H w d w DB h H Zr@Si₁₄ 5. D_{2h} D_{6h} (dbhpb) w w w I 0.16 dbhpa DB K w 5,13,14, w 15. T 16. T w 1200 K, dbhpb dbhpa T 2.72 2.93 Å 2.23 2.42 Å, dbhpb

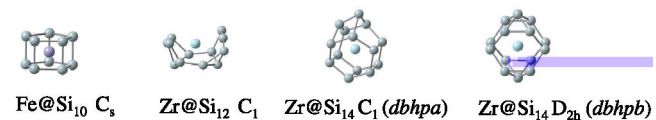


FIG. 2 (). G M- Si_n Zr@Si₁₂ M ≠ 6

T O F . 3() w w O Os@Si₁₀, w

F . 3() . I Zr@Si₁₄, F . 3() . F T II, -2 -1 O , Si₁₀, w Si₁₄, w w O () C - Si₁₀ (Si₁₄) EE O (5.60) (6.18) Si₁₀ Si₁₄, 4 w EE BE M- Si_n (M = W, O, P). I , BE n = 16. B

n = 16, n = 3 12 M = W, n = 14 M = Zr P , n = 12 M = Os. I M , . . . , n = 16, (M = W, n = 15 BE n = 16). H w , w w C w - 10,17 , fi w n = 15 16 14 n = 12 5 Si_n w , n = 14 T Si_n w EE-n BE-n I , EE M- w

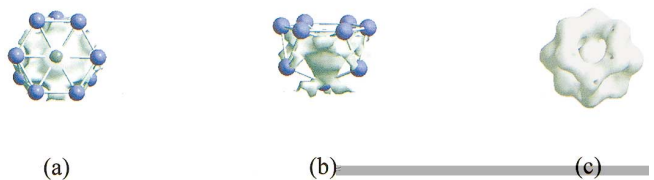


FIG. 3 (). C () Os@Si₁₀ w () w () dbhpb Zr@Si₁₄. T 0.060 0.045 . . Os@Si₁₀ Zr@Si₁₄,

